

GAE

GREAT AMERICAN ELECTROINCS

DM10-28

Silicon NPN high power UHF transistor DM10-28 is designed for common base wide band amplifier, driver, or oscillator applications in land and mobile and on-board radio systems.

Output Power: 10 Watt
Frequency Range: 400-1000 Mhz
Voltage: 28 V
Package Type: 3/8 Helicopter
Input Matched
Common Base Configuration
Emitter Ballast Resistors
Aluminum Metalization

Electrical Characteristics ($T_{CASE}=40^{\circ}C$)

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
P_{out}	$f_o = 1000 \text{ Mhz}/V_{cc}=28V/P_{IN}=2.5W$	10			W
G_p	$f_o = 1000 \text{ Mhz}/V_{cc}=28V/P_{out}=10W$	6	9		dB
λ_c	$f_o = 1000 \text{ Mhz}/V_{cc}=28V/P_{out}=10W$	36	42	60	%

ABSOLUTE MAXIMUM RATINGS ($T_{CASE} = 25^{\circ}C$)

SYMBOL	PARAMETERS	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	50	V
V_{EBO}	Emitter-Base Voltage	4	V
I_c	Continuous Collector Current	1.5	A
P_c	Collector Power Dissipation	17*	W
T_j	Junction Temperature	160	$^{\circ}C$
$R_{th(j-c)}$	Junction-Case Thermal Resistance	7	$^{\circ}C/W$

*For Dynamic Operation $T_{CASE} = 40^{\circ}C$

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